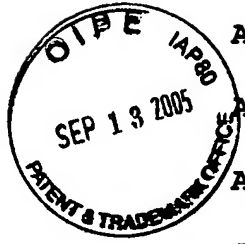


9-14-05

IFW



Appn. Number: 10/609.157

Appn. Filed: Jun/27/2003

Applicant: Hai Jiang

Title: Nono-dot Memory and Fabricating Same

Examiner: Pho M. Luu/2824

Pleasanton, CA. Sept. 12, 2005

**Amendment A**

Commissioner for Patents

P.O. Box 1450

Alexandria, Virginia 22313-1450

Sir,

In response to the Office Action mailed on June 14, 2005,  
please amend the above application as follows:

**1. Drawings:**

**Amendment:** Since the invention is about the structure  
and fabrication of PMCM memory, FIGS 1, 2, 5, 6, 7, 11, 13,  
15 and 16 were deleted. Figures 9 and 10 were combined into